

Silicon PIN Photo Diodes

Model No. PPD-108

Optoelectronic device

◆ Features

- Small & Compact SMD type
- Capable 3-way soldering: front, rear and side plain
- Easy positioning with 2.6x3.2 rectangular hole
- High sensitivity & reliability



◆ Absolute Maximum Ratings

Ta = 25°C

Parameter	Symbol	Value	Unit
DC Reverse Voltage	V _R	20	V
Operating Temperature	Topr	-20 ~ +60	°C
Storage Temperature	Tstg	-30 ~ +80	°C

◆ Electro-optical Characteristics

Ta = 25°C

Parameter	Symbol	MIN	TYP	MAX	Unit	Condition
Sensitive Range	λ	320		1150	nm	Equivalent energy
Peak sensitive wavelength	λ_p		880		nm	Equivalent energy
Short Circuit Current	I _{sc}	100	150	200	nA	100Lx, 2856 ° K
Dark current	I _d	10			pA	V _R =1V. RH≤65%
Shortcircuit current temp. coefficient	β_T		0.2	0.3	%/°C	100Lx, 2856 ° K
Dark current temp. coefficient	α_T		4	5	Times/10°C	V _R =1V. RH≤65%
Terminal capacitance	C _T		20		pF	V _R =0V, f=1MHz

◆ External Dimension (unit: mm)

